

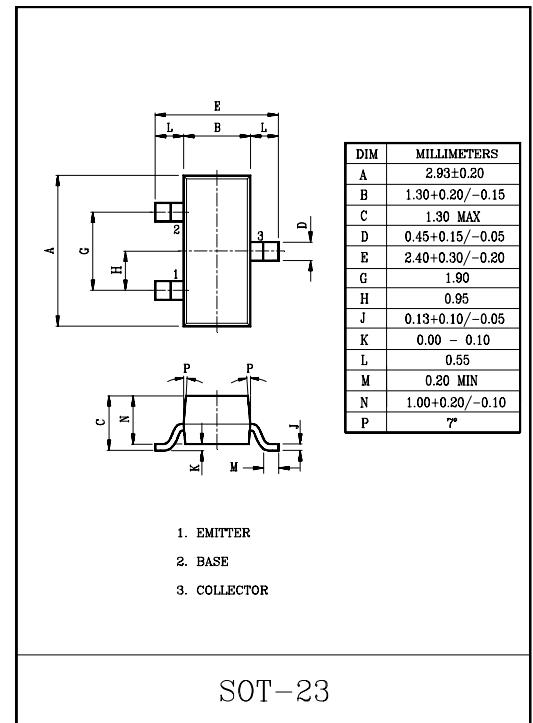
GENERAL PURPOSE APPLICATION.  
SWITCHING APPLICATION.

### FEATURE

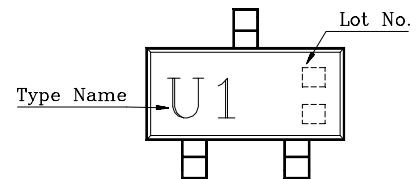
- Super Mini Packaged Transistors for Hybrid Circuits.

### MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CE0}$	50	V
Collector-Emitter Voltage	$V_{CEO}$	45	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	500	mA
Emitter Current	$I_E$	-500	mA
Collector Power Dissipation	$P_C$	310	mW
Junction Temperature	$T_j$	150	°C
Storage Temperature Range	$T_{stg}$	-65~150	°C



### Marking



### ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	45	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C=10\mu A, V_{BE}=0$	50	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	5.0	-	-	V
Collector Cut-off Current	$I_{CBO}$	$V_{CB}=20V, I_E=0$	-	-	100	nA
		$T_a=150^\circ C, V_{CB}=20V, I_E=0$	-	-	5.0	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE}=1V, I_C=100mA$	100	-	600	
		$V_{CE}=1V, I_C=300mA$	70	-	-	
		$V_{CE}=1V, I_C=500mA$	40	-	-	
Base-Emitter Voltage	$V_{BE(ON)}$	$V_{CE}=1V, I_C=500mA$	-	-	1.2	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$	-	-	0.62	V
Transition Frequency	$f_T$	$I_C=10mA, V_{CE}=5V, f=100MHz$	-	200	-	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=10V, f=1MHz$	-	6.0	-	pF